Product Summary

BV_{DSS}	$R_{DS(ON)}$ max	I_D max T_A = +25°C
50V	2.0Ω @ V_{GS} = 5.0V	300mA
	2.5Ω @ V_{GS} = 2.5V	200mA

Features and Benefits

- Low On-Resistance
- Very Low Gate Threshold Voltage (1.0V Max)
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 2kV
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

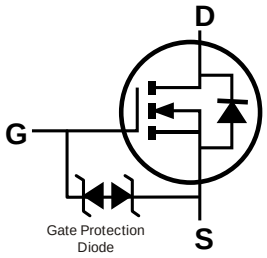
- Load Switches
- Level Switches

Mechanical Data

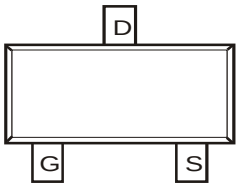
- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Alloy 42 Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

SOT23

Top View



Equivalent Circuit



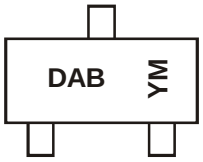
Top View

Ordering Information (Note 5)

Part Number	Case	Packaging
DMN5L06KQ-7	SOT23	3000/Tape & Reel

Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



DAB = Product Type Marking Code
YM = Date Code Marking
Y = Year (ex: G = 2019)
M = Month (ex: 9 = September)

Date Code Key

Year	2006	~	2019	2020	2021	2022	2023	2024	2025	2026	2027	2028
Code	T	~	G	H	I	J	K	L	M	N	O	P

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Drain-Source Voltage		V_{DSS}	50	V
Gate-Source Voltage		V_{GSS}	±20	V
Drain Current (Note 6)	Continuous Pulsed (Note 7)	I_D	300 800	mA
Maximum Body Diode Forward Current (Note 6)		I_S	300	mA

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P_D	350	mW
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	357	°C/W
Operating and Storage Temperature Range	T_J, T_{STG}	-65 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage		BV_{DSS}	50	—	—	V	V_{GS} = 0V, I_D = 10μA
Zero Gate Voltage Drain Current	@ T_C = +25°C	I_{DSS}	—	—	60	nA	V_{DS} = 50V, V_{GS} = 0V
Gate-Body Leakage		I_{GSS}	—	—	1 500 50	μA nA nA	V_{GS} = ±12V, V_{DS} = 0V V_{GS} = ±10V, V_{DS} = 0V V_{GS} = ±5V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage		$V_{GS(TH)}$	0.49	—	1.0	V	V_{DS} = V_{GS}, I_D = 250μA
Static Drain-Source On-Resistance		$R_{DS(ON)}$	— — —	2.0 1.6 1.3	3.0 2.5 2.0	Ω	V_{GS} = 1.8V, I_D = 50mA V_{GS} = 2.5V, I_D = 50mA V_{GS} = 5.0V, I_D = 50mA
On-State Drain Current		$I_{D(ON)}$	0.5	1.4	—	A	V_{GS} = 10V, V_{DS} = 7.5V
Forward Transconductance		$\|Y_{fs}\|$	200	—	—	mS	V_{DS} = 10V, I_D = 0.2A
Source-Drain Diode Forward Voltage		V_{SD}	0.5	0.8	1.4	V	V_{GS} = 0V, I_S = 115mA
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance		C_{iss}	—	—	50	pF	V_{DS} = 25V, V_{GS} = 0V f = 1.0MHz
Output Capacitance		C_{oss}	—	—	25	pF	
Reverse Transfer Capacitance		C_{rss}	—	—	5.0	pF	

Notes:
6. Device mounted on FR-4 PCB.
7. Pulse width ≤10ms, Duty Cycle ≤1%.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

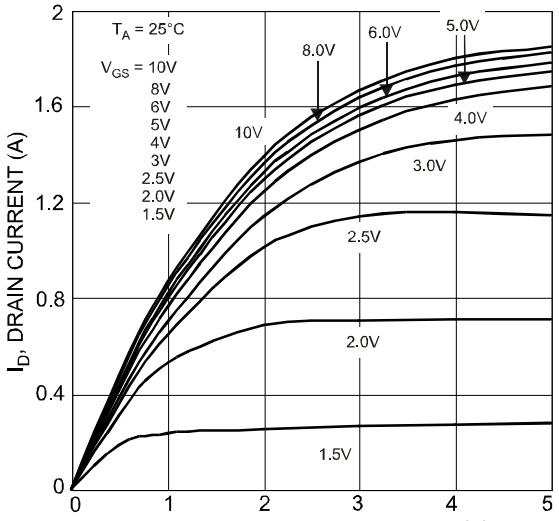


Fig. 1 Typical Output Characteristics

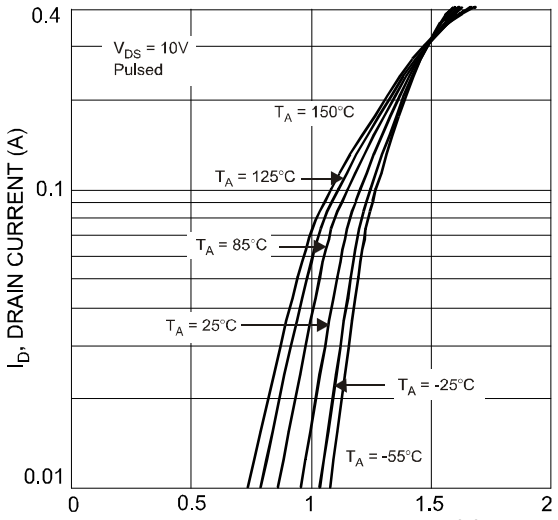


Fig. 2 Typical Transfer Characteristics

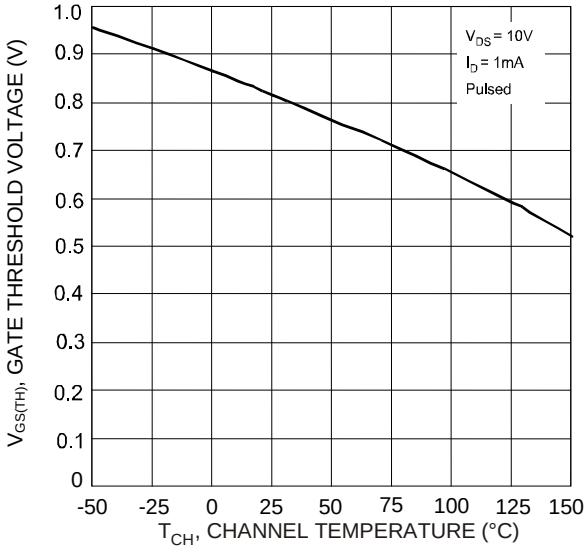


Fig. 3 Gate Threshold Voltage vs. Channel Temperature

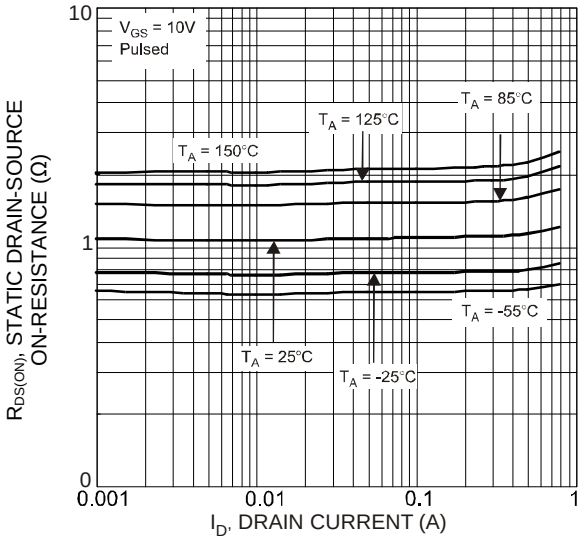


Fig. 4 Static Drain-Source On-Resistance vs. Drain Current

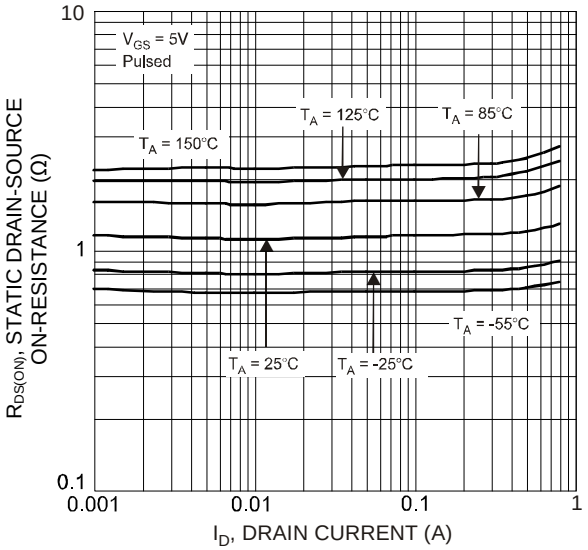


Fig. 5 Static Drain-Source On-Resistance vs. Drain Current

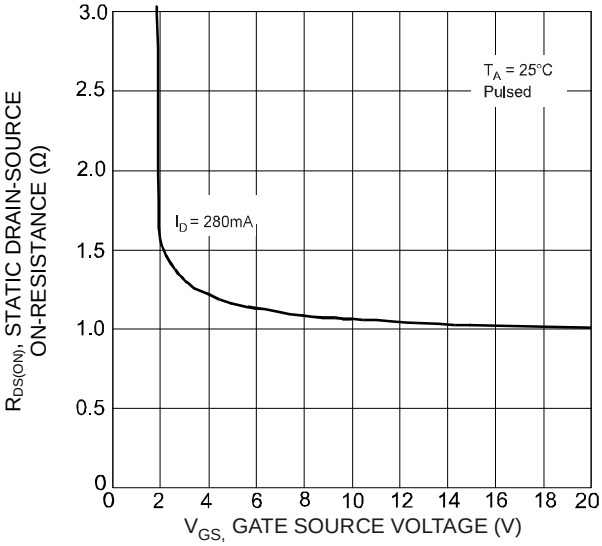


Fig. 6 Static Drain-Source On-Resistance vs. Gate-Source Voltage

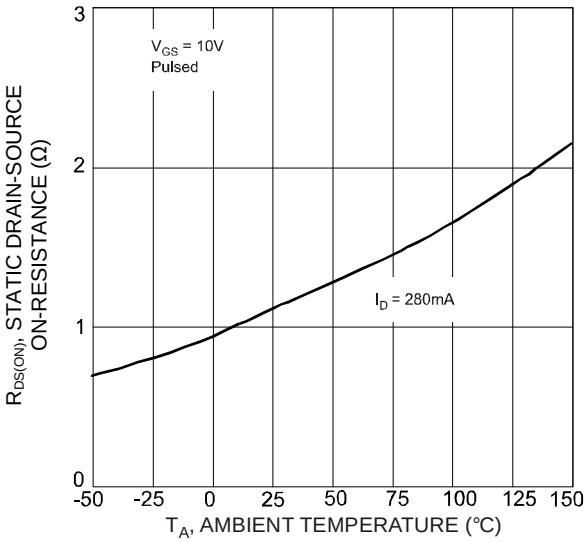


Fig. 7 Static Drain-Source On-State Resistance vs. Ambient Temperature

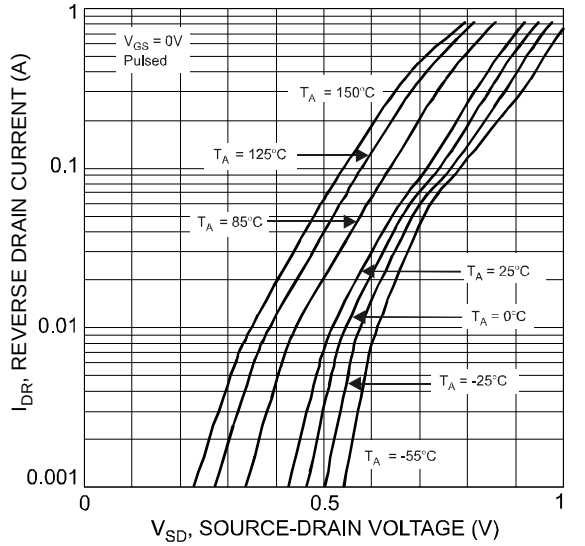


Fig. 8 Reverse Drain Current vs. Source-Drain Voltage

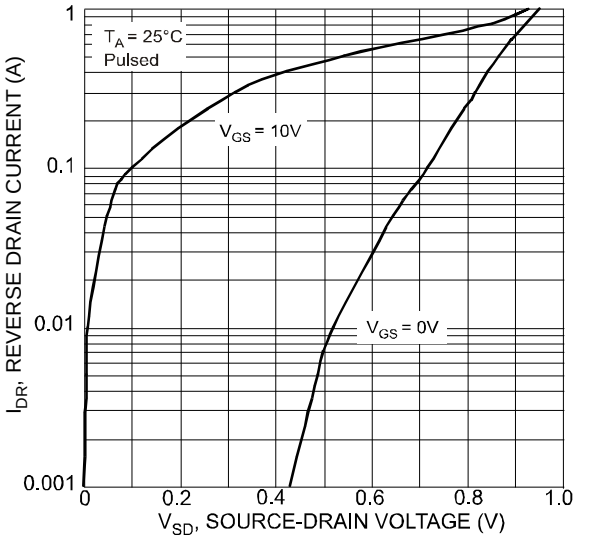


Fig. 9 Reverse Drain Current vs. Source-Drain Voltage

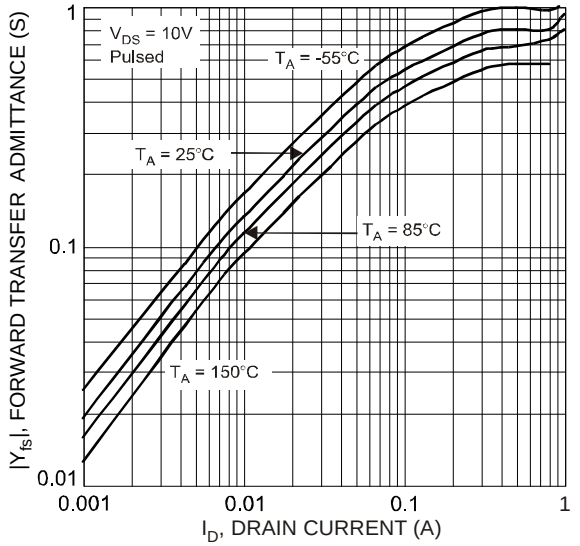


Fig.10 Forward Transfer Admittance vs. Drain Current

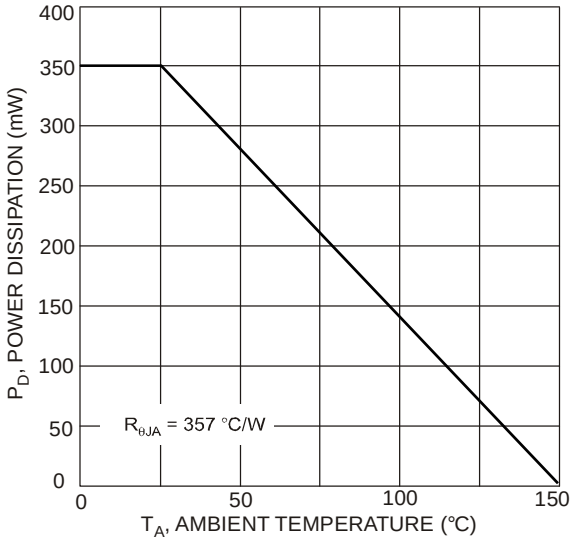


Fig. 11 Derating Curve - Total

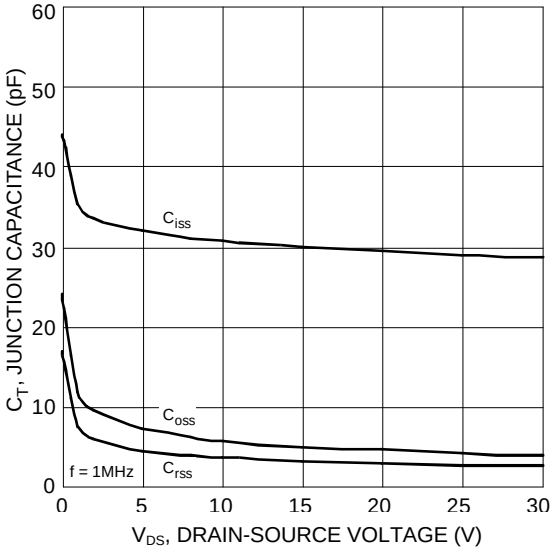
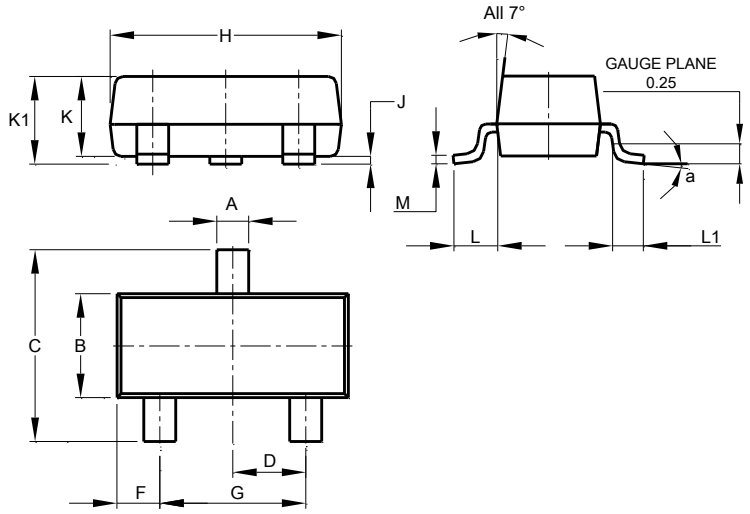


Fig. 12 Typical Junction Temperature

Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

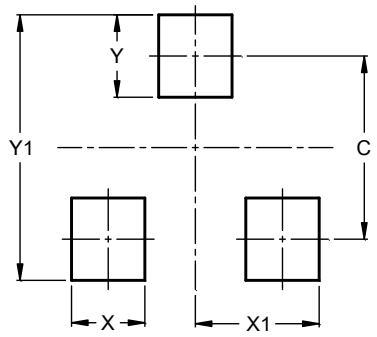


SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	--
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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